



# P-Channel 2.5-V (G-S) MOSFET

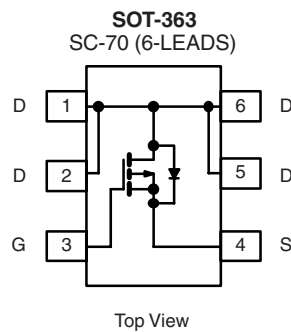
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)
- 20	0.150 at V <sub>GS</sub> = - 4.5 V	- 1.5	2.9
	0.175 at V <sub>GS</sub> = - 3.6 V	- 1.4	
	0.265 at V <sub>GS</sub> = - 2.5 V	- 1.2	

## FEATURES

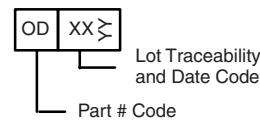
- TrenchFET® Power MOSFET



RoHS  
COMPLIANT



### Marking Code



Ordering Information: Si1403BDL-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V <sub>DS</sub>	- 20		V	
Gate-Source Voltage	V <sub>GS</sub>	± 12			
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	- 1.5	- 1.4	A
		T <sub>A</sub> = 85 °C	- 1.2	- 1.0	
Pulsed Drain Current	I <sub>DM</sub>	- 5			
Continuous Diode Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	- 0.8	- 0.8		
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	0.625	0.568	W
		T <sub>A</sub> = 85 °C	0.400	0.295	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 5 s	165	200	°C/W
		Steady State	180	220	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	105	130		

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.



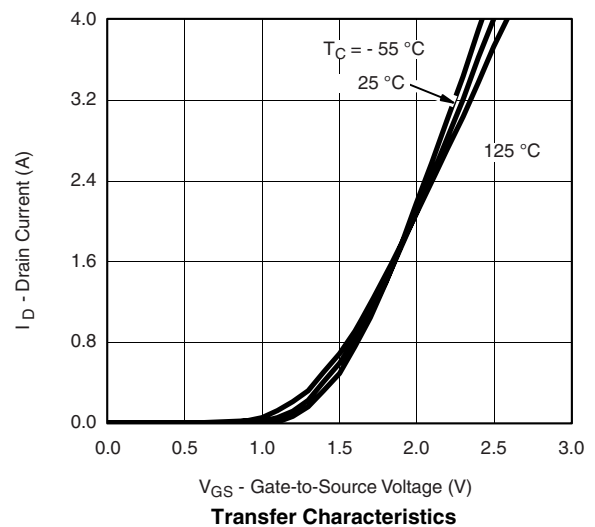
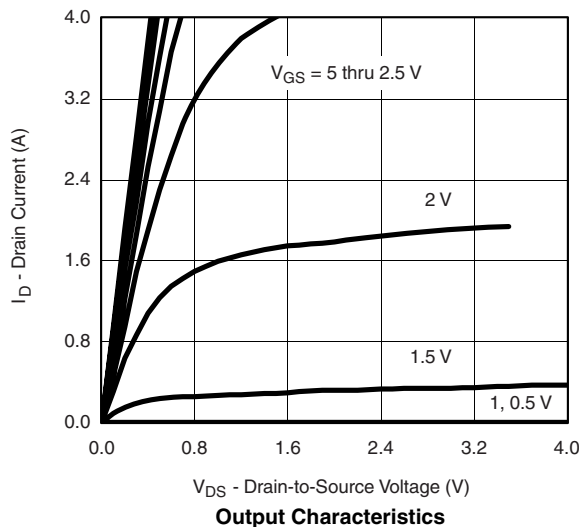
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.6		-1.3	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			-5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-2			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$		0.120	0.150	$\Omega$
		$V_{GS} = -3.6\text{ V}, I_D = -1.4\text{ A}$		0.140	0.175	
		$V_{GS} = -2.5\text{ V}, I_D = -0.8\text{ A}$		0.220	0.265	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10\text{ V}, I_D = -1.5\text{ A}$		3.4		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -0.8\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$		29	4.5	nC
Gate-Source Charge	$Q_{gs}$		0.65			
Gate-Drain Charge	$Q_{gd}$		1.0			
Gate Resistance	$R_g$	$f = 1.0\text{ MHz}$		9		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 6\text{ }\Omega$		13	20	ns
Rise Time	$t_r$		30	45		
Turn-Off Delay Time	$t_{d(off)}$		28	42		
Fall Time	$t_f$		13	20		
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = -0.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		12	25	
Body Diode Reverse Recovery Charge	$Q_{rr}$			4	8	nC

Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

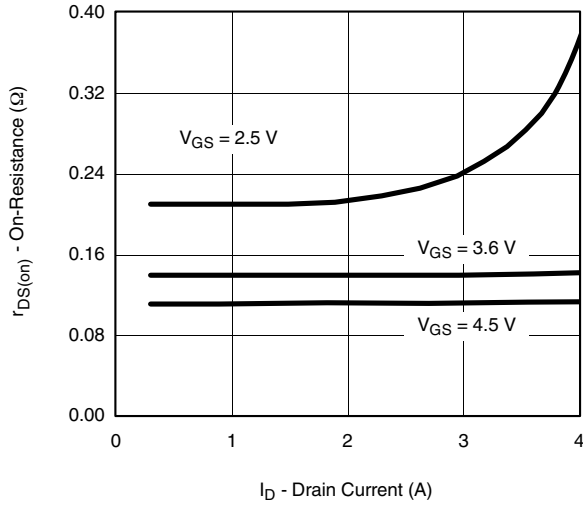
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted

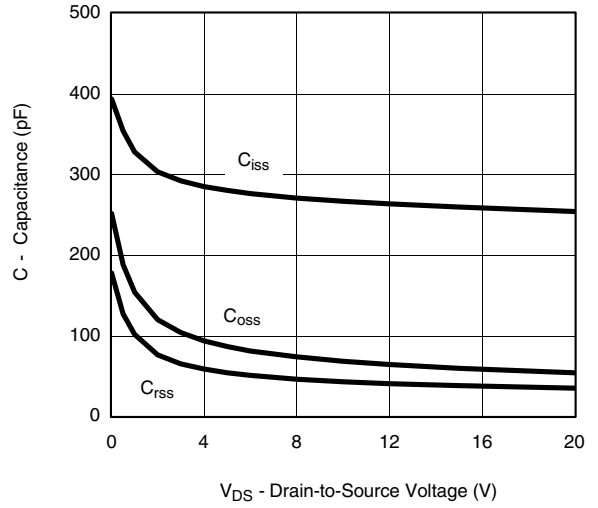




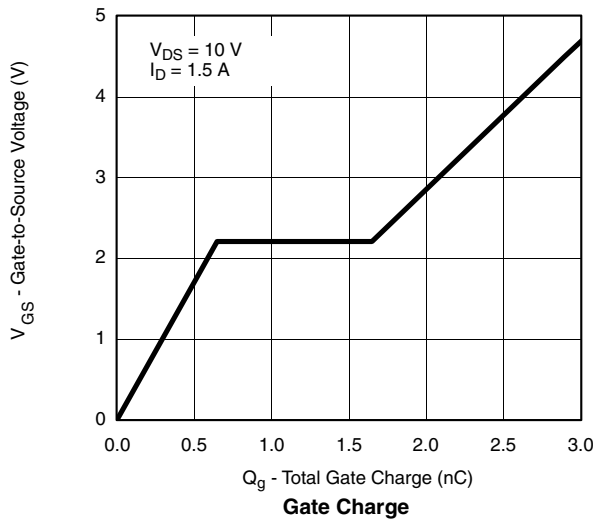
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



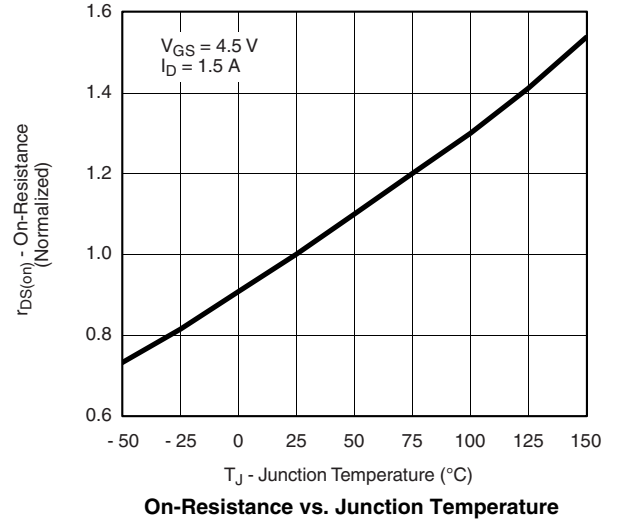
**On-Resistance vs. Drain Current**



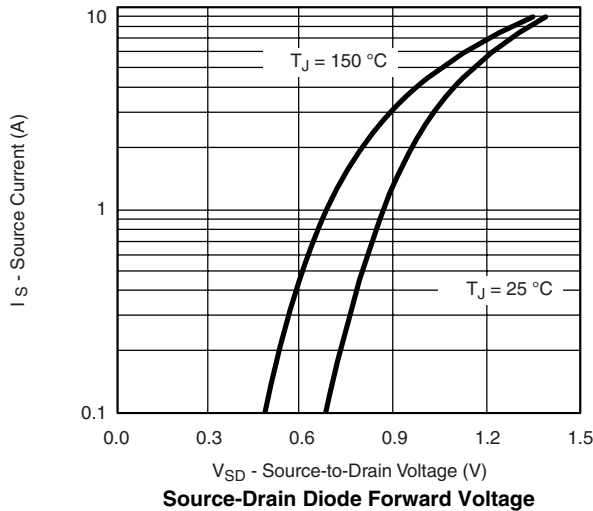
**Capacitance**



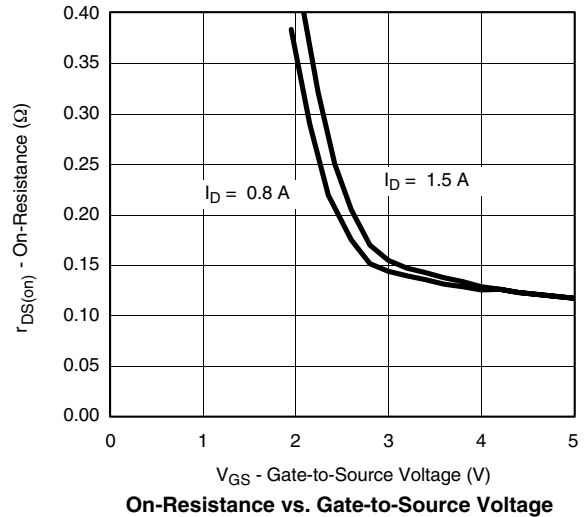
**Gate Charge**



**On-Resistance vs. Junction Temperature**



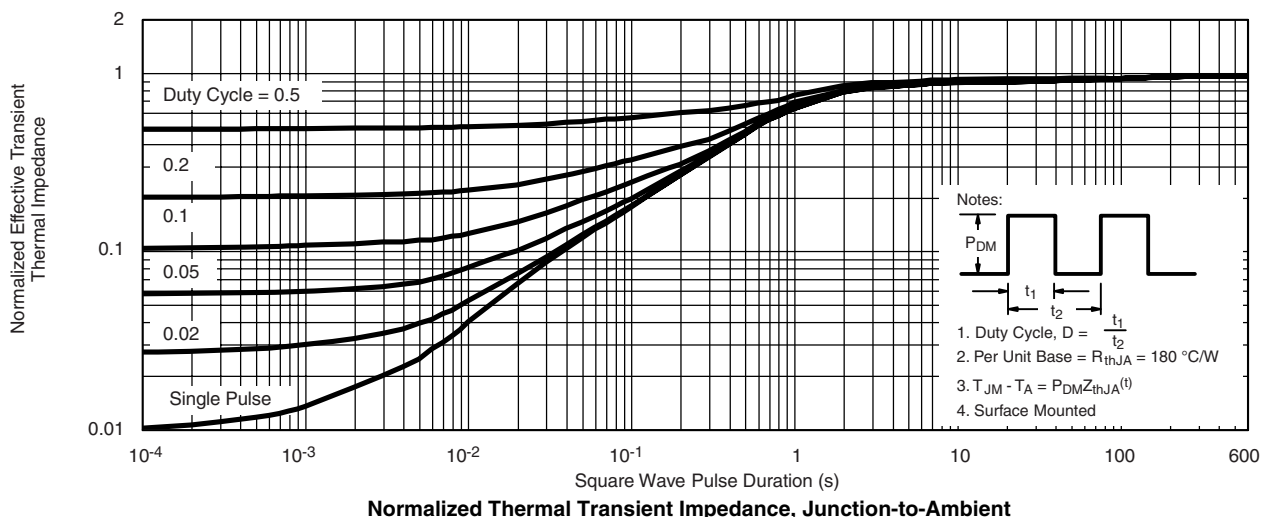
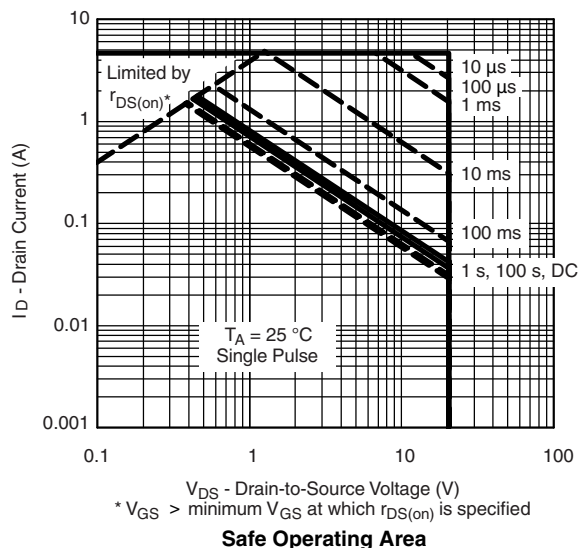
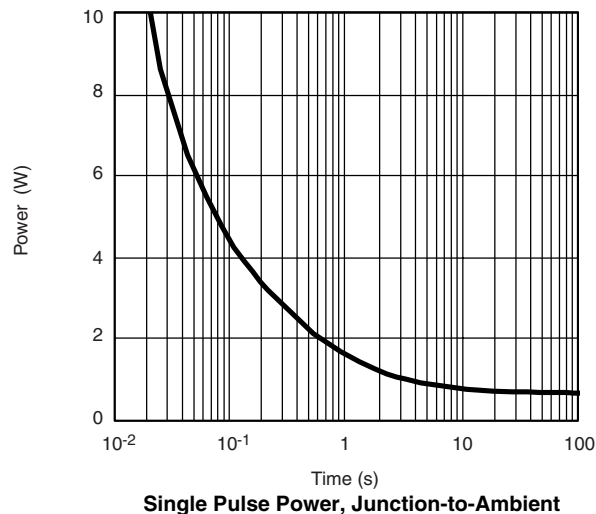
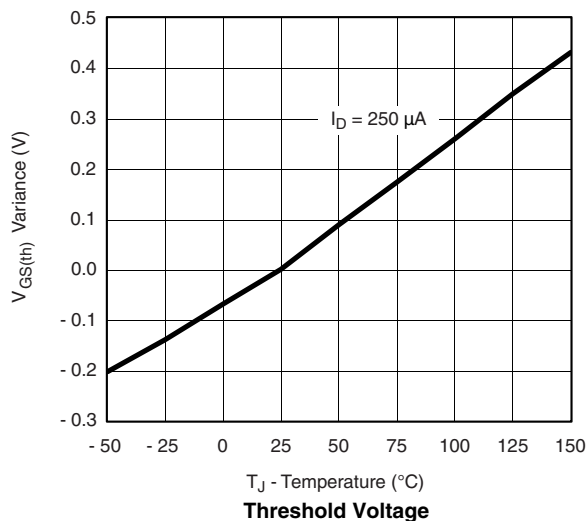
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**

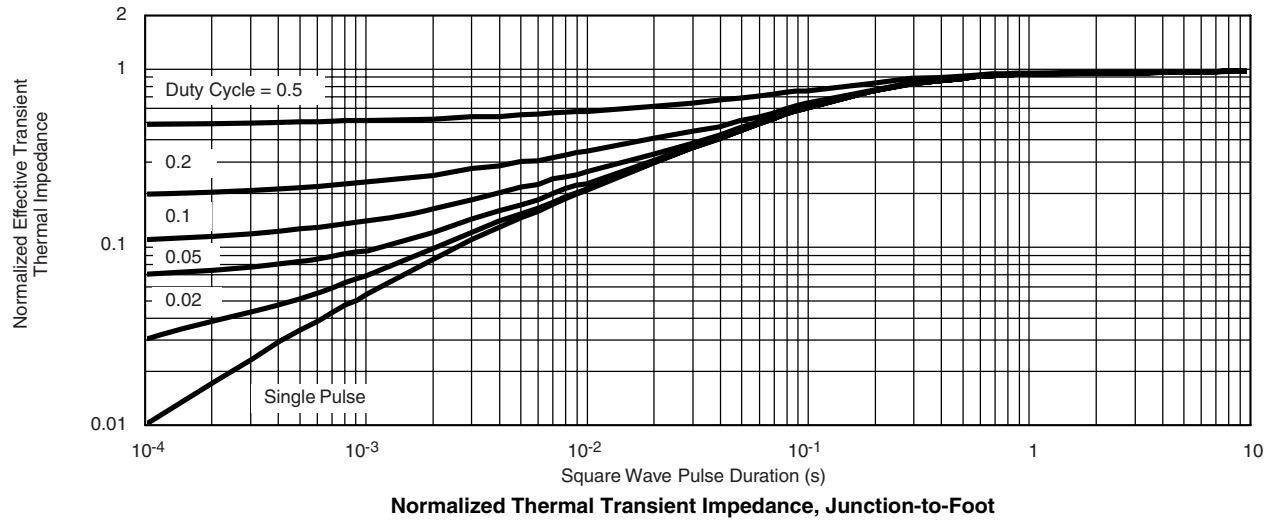


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted





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